



Product Summary

V _{(BR)DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
201/	21mΩ @ V _{GS} = 10V	30A
30V	$35m\Omega @ V_{GS} = 4.5V$	24A

Description

This MOSFET is designed to minimize the on-state resistance $(R_{DS(ON)})$, yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Backlighting
- Power Management Functions
- DC-DC Converters

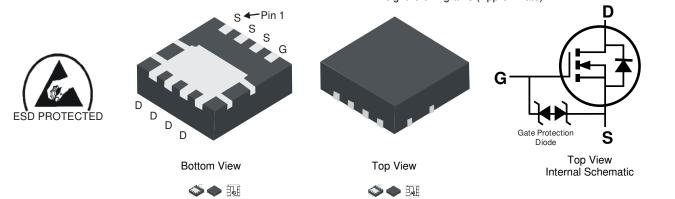
30V N-CHANNEL ENHANCEMENT MODE MOSFET

Features and Benefits

- Low R_{DS(ON)} Ensures On-State Losses are Minimized
- Small form factor thermally efficient package enables higher density end products (PowerDI[®])
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (<u>DMN3018SFGQ</u>)

Mechanical Data

- Case: PowerDI3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe Solderable per MIL-STD-202, Method 208 33
- Weight: 0.072 grams (Approximate)



Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3018SFG-7	PowerDI3333-8	2000/Tape & Reel
DMN3018SFG-13	PowerDI3333-8	3000/Tape & Reel

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

Notes:



N38 = Product Type Marking Code YYWW = Date Code Marking YY = Last Digit of Year (ex: 16 = 2016) WW = Week Code (01 - 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	V _{DSS}	30	V		
Gate-Source Voltage	V _{GSS}	±25	V		
Continuous Drain Current (Note 6) V_{GS} = 10V	Steady State	T _C = +25°C T _C = +70°C	ID	30 25	А
Continuous Drain Current (Note C) V 10V	Steady State	T _A = +25°C T _A = +70°C	ID	8.5 6.8	А
Continuous Drain Current (Note 6) $V_{GS} = 10V$	t<10s	T _A = +25°C T _A = +70°C	ID	11.3 9.1	A
	Steady State	T _A = +25°C T _A = +70°C	ID	6.6 5.3	А
Continuous Drain Current (Note 6) $V_{GS} = 4.5V$	t<10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ID	8.7 7.0	А
Maximum Continuous Body Diode Forward Currer	Is	2.5	А		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1	I _{DM}	60	А		
Avalanche Current (Note 7) L = 0.1mH	I _{AS}	18	А		
Avalanche Energy (Note 7) L = 0.1mH			Eas	16	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Units	
Total Power Dissipation (Note 5)		PD	1.0	W	
Thermal Resistance. Junction to Ambient (Note 5)	Steady State	Deve	126	°C/W	
Thermal Resistance, sunction to Amblent (Note 5)	t<10s	R _{0JA}	71	0/10	
Total Power Dissipation (Note 6)		PD	2.2	W	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Р	56	°C/W	
mermai Resistance, sunction to Ambient (Note 6)	t<10s	R _{0JA}	31		
Thermal Resistance, Junction to Case (Note 6)		R _{ejc}	7.0		
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to 150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	30	—	—	V	$V_{GS} = 0V, I_D = 250 \mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	μA	$V_{DS} = 24V, V_{GS} = 0V$	
Gate-Source Leakage	IGSS	_	—	±10	μA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	1	1.7	2.1	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance	Р	—	16	21	mΩ	$V_{GS} = 10V, I_D = 10A$	
	R _{DS(ON)}	_	21	35	111112	$V_{GS} = 4.5V, I_D = 8.5A$	
Diode Forward Voltage	V _{SD}	0.5	_	1.2	V	$V_{GS} = 0V, I_S = 1A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	CISS	_	697	—	pF		
Output Capacitance	Coss	—	97	-	pF	− V _{DS} = 15V, V _{GS} = 0V, − f = 1.0MHz	
Reverse Transfer Capacitance	C _{RSS}	_	67	—	pF		
Gate resistance	R _G	_	1.47	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Q _G	_	6.0	—	nC		
Total Gate Charge (V _{GS} = 10V)	Q _G	_	13.2	_	nC	$V_{GS} = 10V, V_{DS} = 15V,$	
Gate-Source Charge	Q _{GS}	_	2.2	_	nC	$I_D = 9A$	
Gate-Drain Charge	Q _{GD}	_	1.8	_	nC	1	
Turn-On Delay Time	t _{D(ON)}	_	4.3	_	ns		
Turn-On Rise Time	t _R		4.4	_	ns	$\label{eq:VDD} \begin{split} V_{DD} &= 15V, \ V_{GS} = 10V, \\ R_L &= 15\Omega, I_D = 1A, \ R_G = 6\Omega \end{split}$	
Turn-Off Delay Time	t _{D(OFF)}		20.1	_	ns		
Turn-Off Fall Time	tF	—	4.1	_	ns		
Reverse Recovery Time	T _{RR}	—	7.3	—	ns		
Reverse Recovery Charge	Q _{RR}	—	7.9	—	nC	$I_F = 9A$, di/dt = 500A/µs	

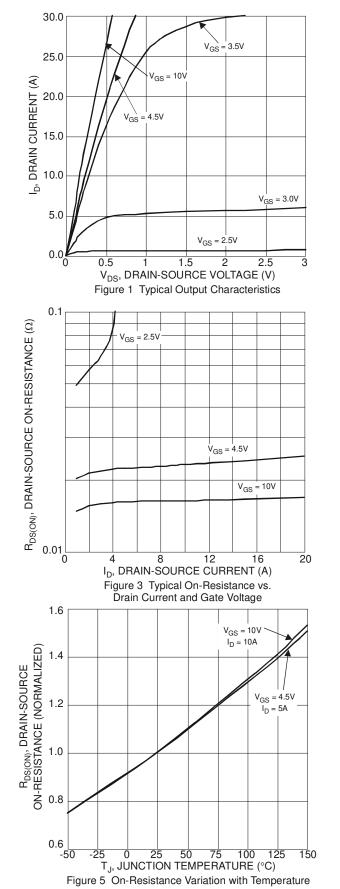
Notes:

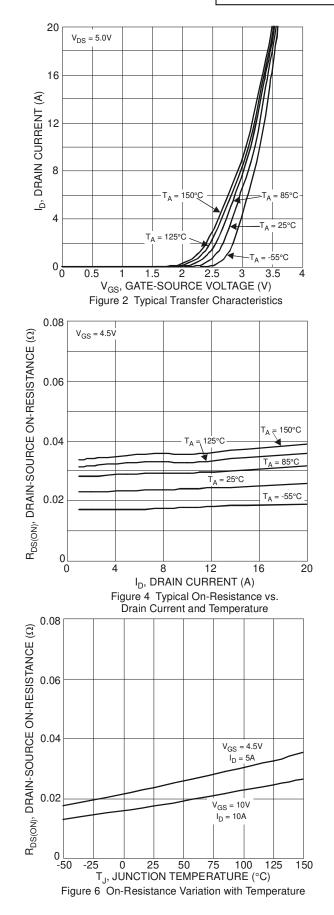
Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.

7. I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep $T_J = +25^{\circ}C$.

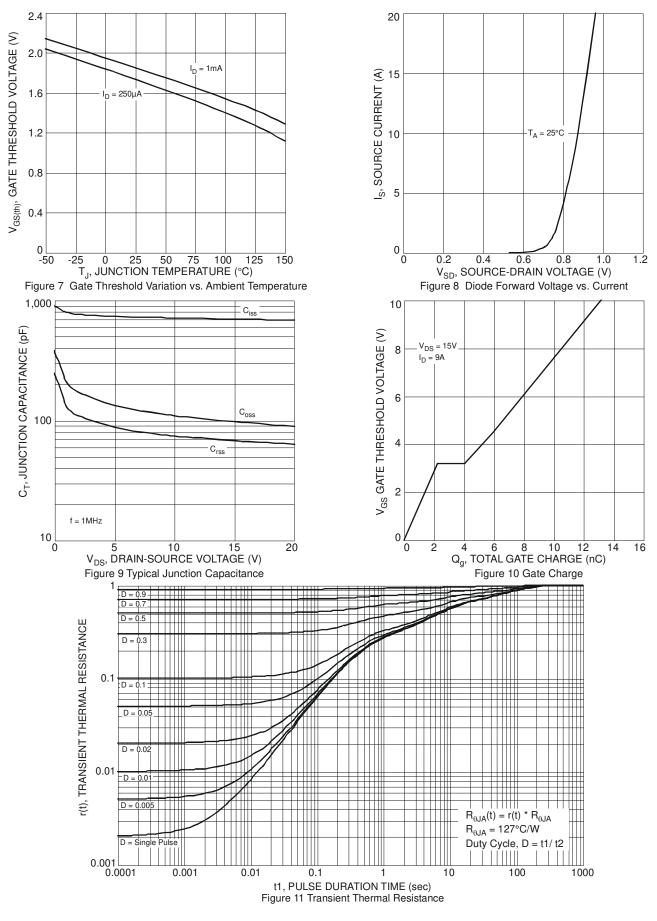
8. Short duration pulse test used to minimize self-heating effect.







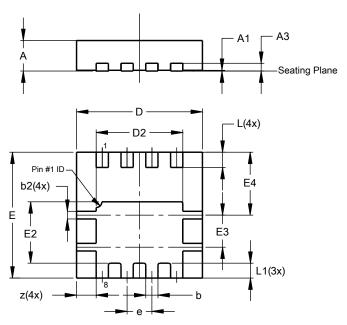






Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

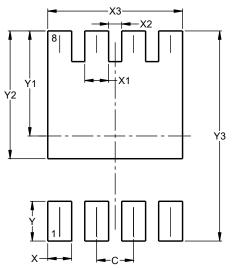


PowerDI3333-8						
Dim	Min	Max	Тур			
Α	0.75	0.85	0.80			
A1	0.00	0.05	0.02			
A3	-	-	0.203			
b	0.27	0.37	0.32			
b2	0.15	0.25	0.20			
D	3.25	3.35	3.30			
D2	2.22	2.32	2.27			
Е	3.25	3.35	3.30			
E2	1.56	1.66	1.61			
E3	0.79	0.89	0.84			
E4	1.60	1.70	1.65			
е	-	-	0.65			
L	0.35	0.45	0.40			
L1	_	_	0.39			
z	_	-	0.515			
All I	All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8



Dimensions	Value (in mm)
С	0.650
Х	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700

PowerDI3333-8



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